Laurence Eaves

List of Publications by Year
in descending order

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456 papers	16,942 citations	28274 55 h-index	18647 119 g-index
459 all docs	459 docs citations	459 times ranked	13997 citing authors

#	Article	IF	Citations
1	Field-Effect Tunneling Transistor Based on Vertical Graphene Heterostructures. Science, 2012, 335, 947-950.	12.6	2,268
2	Vertical field-effect transistor based on grapheneâ€“WS2 heterostructures for flexible and transparent electronics. Nature Nanotechnology, 2013, 8, 100-103.	31.5	1,543
3	High electron mobility, quantum Hall effect and anomalous optical response in atomically thin InSe. Nature Nanotechnology, 2017, 12, 223-227.	31.5	996
4	Electron Tunneling through Ultrathin Boron Nitride Crystalline Barriers. Nano Letters, 2012, 12, 1707-1710.	9.1	724
5	Resonant tunnelling and negative differential conductance in graphene transistors. Nature Communications, 2013, 4, 1794.	12.8	542
6	Tuning the Bandgap of Exfoliated InSe Nanosheets by Quantum Confinement. Advanced Materials, 2013, 25, 5714-5718.	21.0	512
7	Twist-controlled resonant tunnelling in graphene/boron nitride/graphene heterostructures. Nature Nanotechnology, 2014, 9, 808-813.	31.5	435
8	High Broadâ€Band Photoresponsivity of Mechanically Formed InSeâ€“Graphene van der Waals Heterostructures. Advanced Materials, 2015, 27, 3760-3766.	21.0	320
9	Magnon-assisted tunnelling in van der Waals heterostructures based on CrBr3. Nature Electronics, 2018, 1, 344-349.	26.0	239
10	Probing the hole dispersion curves of a quantum well using resonant magnetotunneling spectroscopy. Physical Review Letters, 1991, 66, 1749-1752.	7.8	213
11	Resonant tunneling through the bound states of a single donor atom in a quantum well. Physical Review Letters, 1992, 68, 1754-1757.	7.8	213
12	Magnetic field studies of elastic scattering and optic-phonon emission in resonant-tunneling devices. Physical Review B, 1989, 39, 3438-3441.	3.2	187
13	Imaging the Electron Wave Function in Self-Assembled Quantum Dots. Science, 2000, 290, 122-124.	12.6	168
14	Direct band-gap crossover in epitaxial monolayer boron nitride. Nature Communications, 2019, 10, 2639.	12.8	162
15	Fermi-edge singularity in resonant tunneling. Physical Review Letters, 1994, 72, 2061-2064.	7.8	160
16	The direct-to-indirect band gap crossover in two-dimensional van der Waals Indium Selenide crystals. Scientific Reports, 2016, 6, 39619.	3.3	150
17	Electron-concentration-dependent quantum-well luminescence: Evidence for a negatively charged exciton. Physical Review B, 1995, 51, 7969-7972.	3.2	149
18	Investigation of theDXcenter in heavily dopedn-GaAs. Physical Review Letters, 1987, 59, 815-818.	7.8	147

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19	Character of states near the Fermi level in (Ga,Mn)As: Impurity to valence band crossover. Physical Review B, 2007, 76, .	3.2	139
20	Magnetoresistance of a two-dimensional electron gas in a strong periodic potential. Physical Review B, 1990, 42, 9229-9232.	3.2	136
21	Chaotic electron diffusion through stochastic webs enhances current flow in superlattices. Nature, 2004, 428, 726-730.	27.8	117
22	High-temperature quantum oscillations caused by recurring Bloch states in graphene superlattices. Science, 2017, 357, 181-184.	12.6	117
23	An investigation of the deep level photoluminescence spectra of InP(Mn), InP(Fe), and of undoped InP. Journal of Applied Physics, 1982, 53, 4955-4963.	2.5	105
24	Manifestations of Classical Chaos in the Energy Level Spectrum of a Quantum Well. Physical Review Letters, 1995, 75, 1142-1145.	7.8	105
25	Magnetotunneling spectroscopy of a quantum well in the regime of classical chaos. Physical Review Letters, 1994, 72, 2608-2611.	7.8	102
26	Sequential tunneling due to intersubband scattering in doubleâ€barrier resonant tunneling devices. Applied Physics Letters, 1988, 52, 212-214.	3.3	101
27	Probing the wave function of quantum confined states by resonant magnetotunneling. Physical Review B, 1993, 48, 5664-5667.	3.2	92
28	Tuning the valley and chiral quantum state of Dirac electrons in van der Waals heterostructures. Science, 2016, 353, 575-579.	12.6	88
29	Observations of Magnetoquantized Interface States by Electron Tunneling in Single-Barriernâ^'(InGa)Asâ^'InPâ^'n+(InGa)AsHeterostructures. Physical Review Letters, 1987, 59, 2806-2809.	7.8	87
30	Alignment of Aromatic Peptide Tubes in Strong Magnetic Fields. Advanced Materials, 2007, 19, 4474-4479.	21.0	87
31	Electronic structure of self-assembled InAs quantum dots in GaAs matrix. Applied Physics Letters, 1998, 73, 1092-1094.	3.3	86
32	Far infrared photoconductivity from majority and minority impurities in high purity Si and Ge. Solid State Communications, 1974, 15, 1403-1408.	1.9	80
33	Magnetic field studies of negative differential conductivity in double barrier resonant tunnelling structures based on n-InP/(InGa)As. Solid-State Electronics, 1988, 31, 707-710.	1.4	80
34	Electronic processes in double-barrier resonant-tunneling structures studied by photoluminescence spectroscopy in zero and finite magnetic fields. Physical Review B, 1990, 41, 10754-10766.	3.2	80
35	Phonon-Assisted Resonant Tunneling of Electrons in Grapheneâ€“Boron Nitride Transistors. Physical Review Letters, 2016, 116, 186603.	7.8	78
36	Linear magnetoresistance due to multiple-electron scattering by low-mobility islands in an inhomogeneous conductor. Nature Communications, 2012, 3, 1097.	12.8	76

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37	Fourier analysis of magnetophonon and two-dimensional Shubnikov-de Haas magnetoresistance structure. Journal of Physics C: Solid State Physics, 1975, 8, 1034-1053.	1.5	75
38	Observation of space-charge bulk-up and thermalisation in an asymmetric double-barrier resonant tunnelling structure. Journal of Physics Condensed Matter, 1989, 1, 10605-10611.	1.8	75
39	Charge build-up and intrinsic bistability in an asymmetric resonant-tunnelling structure. Semiconductor Science and Technology, 1988, 3, 1060-1062.	2.0	71
40	Room Temperature Electroluminescence from Mechanically Formed van der Waals IIIâ€“VI Homojunctions and Heterojunctions. Advanced Optical Materials, 2014, 2, 1064-1069.	7.3	71
41	Floating gold in cryogenic oxygen. Nature, 2003, 422, 579-579.	27.8	70
42	Nonaxisymmetric Shapes of a Magnetically Levitated and Spinning Water Droplet. Physical Review Letters, 2008, 101, 234501.	7.8	68
43	Resonant tunnelling between the chiral Landau states of twisted graphene lattices. Nature Physics, 2015, 11, 1057-1062.	16.7	64
44	Electrical and spectroscopic studies of space-charged buildup, energy relaxation and magnetically enhanced bistability in resonant-tunneling structures. Solid-State Electronics, 1989, 32, 1101-1108.	1.4	63
45	Observation of intrinsic tristability in a resonant tunneling structure. Applied Physics Letters, 1994, 64, 1248-1250.	3.3	63
46	High-order fractal states in graphene superlattices. Proceedings of the National Academy of Sciences of the United States of America, 2018, 115, 5135-5139.	7.1	63
47	The oscillatory magnetoresistance of electrons in a square superlattice potential. Journal of Physics Condensed Matter, 1989, 1, 8257-8262.	1.8	60
48	New nonlocal magnetoresistance effect at the crossover between the classical and quantum transport regimes. Physical Review Letters, 1991, 67, 3014-3017.	7.8	60
49	Measuring the Probability Density of Quantum Confined States. Physical Review Letters, 1995, 75, 1996-1999.	7.8	60
50	Hexagonal Boron Nitride Tunnel Barriers Grown on Graphite by High Temperature Molecular Beam Epitaxy. Scientific Reports, 2016, 6, 34474.	3.3	60
51	Ligandâ€induced Control of Photoconductive Gain and Doping in a Hybrid Grapheneâ€“Quantum Dot Transistor. Advanced Electronic Materials, 2015, 1, 1500062.	5.1	59
52	Quantum confined acceptors and donors in InSe nanosheets. Applied Physics Letters, 2014, 105, 221909.	3.3	58
53	Graphene-hexagonal boron nitride resonant tunneling diodes as high-frequency oscillators. Applied Physics Letters, 2015, 107, .	3.3	58
54	Photoluminescence and impurity concentration in GaxIn1â^'xAsyP1â^'yalloys latticeâ€matched to InP. Journal of Applied Physics, 1983, 54, 1037-1047.	2.5	57

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55	Observation of spin splitting in single InAs self-assembled quantum dots in AlAs. Applied Physics Letters, 1998, 73, 354-356.	3.3	57
56	Universal conductance fluctuations in the magnetoresistance of submicron-size n+-GaAs wires and laterally confined nâ˜'-GaAs/(AlGa)As heterostructures. Surface Science, 1988, 196, 52-58.	1.9	54
57	Current bistability in double-barrier resonant-tunneling devices. Physical Review B, 1989, 39, 6205-6207.	3.2	53
58	Currentâ€“voltage instabilities in GaN/AlGaN resonant tunnelling structures. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 2389-2392.	0.8	52
59	Breakdown of universal scaling of conductance fluctuations in high magnetic fields. Physical Review Letters, 1992, 69, 1248-1251.	7.8	49
60	Strain-Engineered Graphene Grown on Hexagonal Boron Nitride by Molecular Beam Epitaxy. Scientific Reports, 2016, 6, 22440.	3.3	49
61	High-Field Resonant Magnetotransport Measurements in Smalln+nn+GaAs Structures: Evidence for Electric-Field-Induced Elastic Inter-Landau-Level Scattering. Physical Review Letters, 1984, 53, 608-611.	7.8	48
62	Evidence against the negative-charge-state model for theDXcenter inn-type GaAs. Physical Review Letters, 1989, 62, 1922-1922.	7.8	48
63	Resonant tunneling through donor molecules. Physical Review B, 1994, 50, 8074-8077.	3.2	47
64	Thermal effects in quantum dot lasers. Journal of Applied Physics, 1999, 85, 625-627.	2.5	47
65	Microgravity simulation by diamagnetic levitation: effects of a strong gradient magnetic field on the transcriptional profile of Drosophila melanogaster. BMC Genomics, 2012, 13, 52.	2.8	47
66	Optical properties and device applications of (InGa)As self-assembled quantum dots grown on (311)B GaAs substrates. Applied Physics Letters, 1998, 73, 1415-1417.	3.3	46
67	Piezoelectric effects in In0.5Ga0.5As self-assembled quantum dots grown on (311)B GaAs substrates. Applied Physics Letters, 2000, 77, 2979-2981.	3.3	45
68	Excitation mechanisms of photoluminescence in double-barrier resonant-tunneling structures. Physical Review B, 1990, 42, 3069-3076.	3.2	44
69	Giant Quantum Hall Plateau in Graphene Coupled to an InSe van der Waals Crystal. Physical Review Letters, 2017, 119, 157701.	7.8	44
70	Temperature dependence of magnetoresistance oscillations in a two-dimensional electron gas subjected to a periodic potential. Physical Review B, 1990, 42, 9689-9692.	3.2	43
71	The magnetophonon effect in epitaxial films of n-type inp. Journal of Physics C: Solid State Physics, 1971, 4, L42-L47.	1.5	42
72	High-temperature light emission from InAs quantum dots. Applied Physics Letters, 1999, 75, 814-816.	3.3	42

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73	Vibrations of a diamagnetically levitated water droplet. Physical Review E, 2010, 81, 056312.	2.1	41
74	High-resolution optical absorption spectroscopy on Cr-related defects in GaAs and GaP. Journal of Physics C: Solid State Physics, 1982, 15, 1337-1343.	1.5	40
75	Breakup of the conduction band structure of diluteGaAs1â^'yNyalloys. Physical Review B, 2005, 71, .	3.2	40
76	Cryogenically enhanced magneto-Archimedes levitation. New Journal of Physics, 2005, 7, 118-118.	2.9	40
77	Lattice-Matched Epitaxial Graphene Grown on Boron Nitride. Nano Letters, 2018, 18, 498-504.	9.1	39
78	Hot-electron magnetophonon spectroscopy on micron- and sub-micron-size n+nn+GaAs structures. Journal of Physics C: Solid State Physics, 1984, 17, 6177-6190.	1.5	38
79	Comment on â€œAlN/GaN double-barrier resonant tunneling diodes grown by rf-plasma-assisted molecular-beam epitaxyâ€•[Appl. Phys. Lett. 81, 1729 (2002)]. Applied Physics Letters, 2003, 83, 3626-3627.	3.3	37
80	Inter-Landau-level transitions of resonantly tunnelling electrons in tilted magnetic fields. Semiconductor Science and Technology, 1991, 6, 1021-1024.	2.0	36
81	Resonant Magnetotunneling via One-Dimensional Quantum Confined States. Physical Review Letters, 1994, 73, 1146-1149.	7.8	36
82	Carrier thermalization within a disordered ensemble of self-assembled quantum dots. Physical Review B, 2000, 62, 11084-11088.	3.2	36
83	Tailoring the electronic properties of GaAs/AlAs superlattices by InAs layer insertions. Applied Physics Letters, 2002, 81, 661-663.	3.3	36
84	Strain relaxation in stacked InAs/GaAs quantum dots studied by Raman scattering. Applied Physics Letters, 2003, 83, 3069-3071.	3.3	36
85	Microscopic Analysis of the Valence Band and Impurity Band Theories of (Ga,Mn)As. Physical Review Letters, 2010, 105, 227202.	7.8	36
86	A model for some defect-related bound exciton lines in the photoluminescence spectrum of GaAs layers grown by molecular beam epitaxy. Journal of Physics C: Solid State Physics, 1984, 17, L705-L709.	1.5	35
87	Oscillatory structures in GaAs/(AlGa)As tunnel junctions. Physical Review Letters, 1985, 55, 262-262.	7.8	35
88	Field-effect control of tunneling barrier height by exploiting graphene's low density of states. Journal of Applied Physics, 2013, 113, .	2.5	35
89	Plasmon assisted resonant tunneling in a double barrier heterostructure. Physical Review Letters, 1994, 72, 3397-3400.	7.8	34
90	Submicrometer resonant tunnelling diodes fabricated by photolithography and selective wet etching. Applied Physics Letters, 1994, 65, 1124-1126.	3.3	34

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91	Quantum-dot phonons in self-assembled InAs/GaAs quantum dots: Dependence on the coverage thickness. Applied Physics Letters, 2000, 77, 3556-3558.	3.3	34
92	A study of intervalley scattering in n-Si by the magnetophonon effect. Solid State Communications, 1974, 14, 1241-1245.	1.9	33
93	An energy scheme for interpreting deep-level photoconductivity and other recent optical measurement for Fe-doped InP. Journal of Physics C: Solid State Physics, 1981, 14, 5063-5068.	1.5	33
94	Emission of electrons from the ground and first excited states of self-organized InAs/GaAs quantum dot structures. Journal of Electronic Materials, 1999, 28, 486-490.	2.2	33
95	Terahertz response of hot electrons in dilute nitride Ga(AsN) alloys. Applied Physics Letters, 2006, 88, 032107.	3.3	33
96	Subterahertz Acoustical Pumping of Electronic Charge in a Resonant Tunneling Device. Physical Review Letters, 2012, 108, 226601.	7.8	33
97	Meristematic cell proliferation and ribosome biogenesis are decoupled in diamagnetically levitated Arabidopsis seedlings. BMC Plant Biology, 2013, 13, 124.	3.6	33
98	Tunnel spectroscopy of localised electronic states in hexagonal boron nitride. Communications Physics, 2018, 1, .	5.3	33
99	Positive Identification of theCr4+â†'Cr3+Thermal Transition in GaAs. Physical Review Letters, 1982, 49, 1728-1731.	7.8	32
100	Controlling the shape of InAs self-assembled quantum dots by thin GaAs capping layers. Journal of Crystal Growth, 2003, 251, 155-160.	1.5	32
101	Two-Dimensional Covalent Crystals by Chemical Conversion of Thin van der Waals Materials. Nano Letters, 2019, 19, 6475-6481.	9.1	32
102	High-magnetic-field Zeeman spectroscopy of the 0.84-eV Cr-related emission and absorption line in GaAs(Cr): Experiment and theory. Physical Review B, 1982, 26, 4473-4484.	3.2	31
103	Electron conduction in two-dimensionalGaAs1â^'yNychannels. Physical Review B, 2004, 69, .	3.2	31
104	High-temperature molecular beam epitaxy of hexagonal boron nitride layers. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2018, 36, .	1.2	31
105	Magnetic breakdown of a two-dimensional electron gas in a periodic potential. Physical Review B, 1991, 43, 9980-9983.	3.2	30
106	Electroluminescence and impact ionization phenomena in a doubleâ€barrier resonant tunneling structure. Applied Physics Letters, 1991, 58, 1164-1166.	3.3	30
107	Diamagnetic levitation enhances growth of liquid bacterial cultures by increasing oxygen availability. Journal of the Royal Society Interface, 2011, 8, 334-344.	3.4	30
108	Hybrid magneto-electric states in resonant tunnelling structures. Superlattices and Microstructures, 1989, 5, 527-530.	3.1	29

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109	Zeroâ€dimensional states in macroscopic resonant tunneling devices. Applied Physics Letters, 1994, 64, 2563-2565.	3.3	29
110	Intrinsic and deepâ€level photoacoustic spectroscopy of GaAs (Cr) and of other bulk semiconductors. Applied Physics Letters, 1981, 38, 768-770.	3.3	28
111	Edge channels and the quantum-Hall-effect breakdown. Physical Review B, 1994, 49, 5379-5385.	3.2	28
112	Theory of resonant tunneling through a quantum wire. Physical Review B, 1995, 51, 1735-1742.	3.2	28
113	Indium interdiffusion in annealed and implanted InAs/(AlGa)As self-assembled quantum dots. Journal of Applied Physics, 2001, 89, 6044-6047.	2.5	28
114	Hot-electrons and negative differential conductance inGaAs1â^'xNx. Physical Review B, 2005, 72, .	3.2	28
115	Evidence for sequential tunnelling and charge build-up in double barrier resonant tunnelling devices. Surface Science, 1988, 196, 404-409.	1.9	27
116	Bifurcations and chaos in semiconductor superlattices with a tilted magnetic field. Physical Review E, 2008, 77, 026209.	2.1	27
117	Effect of low nitrogen concentrations on the electronic properties of<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>InAs</mml:mtext></mml:mrow><mml:mrow><mml:mn>1</mml:mn> Physical Review B, 2009, 80, .	3.2	27
118	Nonlinear Far-Infrared Magnetoabsorption and Optically Detected Magnetoimpurity Effect inn-GaAs. Physical Review Letters, 1983, 50, 1309-1312.	7.8	26
119	The resistance of two quantum point contacts in series. Journal of Physics Condensed Matter, 1989, 1, 7505-7511.	1.8	26
120	Electroluminescence investigations of electron and hole resonant tunneling inp-i-ndouble-barrier structures. Physical Review B, 1992, 45, 9513-9516.	3.2	26
121	Influence of high-index GaAs substrates on the growth of highly strained (InGa)As/GaAs heterostructures. Journal of Crystal Growth, 1999, 201-202, 276-279.	1.5	26
122	A study of intervalley scattering in n-Si by stress-dependent longitudinal magnetophonon resonance. Solid State Communications, 1974, 15, 1281-1285.	1.9	25
123	Resonant tunnelling studies of magnetoelectric quantisation in wide quantum wells. Journal of Physics Condensed Matter, 1989, 1, 4865-4871.	1.8	25
124	Landau-level pinning in wide modulation-doped quantum-well structures in the integer quantum Hall regime. Physical Review B, 1991, 44, 3436-3439.	3.2	25
125	Edge effects in a gated submicron resonant tunneling diode. Applied Physics Letters, 1992, 60, 2508-2510.	3.3	25
126	Introduction. Carbon-based electronics: fundamentals and device applications. Philosophical Transactions Series A, Mathematical, Physical, and Engineering Sciences, 2008, 366, 189-193.	3.4	25

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127	Strong magnetophonon oscillations in extra-large graphene. Nature Communications, 2019, 10, 3334.	12.8	25
128	A review of the magneto-impurity effect in semiconductors. Journal of Physics C: Solid State Physics, 1979, 12, 2809-2828.	1.5	24
129	Probing the anisotropic dispersion of hole states in (100) and (311)A AlAs/GaAs/AlAs quantum wells. Semiconductor Science and Technology, 1994, 9, 298-309.	2.0	24
130	Hole spaceâ€charge buildup and evidence for sequential tunneling inpâ€type doubleâ€barrier resonant tunneling devices. Applied Physics Letters, 1992, 60, 1474-1476.	3.3	23
131	Evidence for quantum states corresponding to families of stable and chaotic classical orbits in a wide potential well. Physical Review B, 1995, 51, 18029-18032.	3.2	23
132	Time-resolved photoluminescence of InAs quantum dots in a GaAs quantum well. Applied Physics Letters, 2004, 84, 3046-3048.	3.3	23
133	Electric-field inversion asymmetry: Rashba and Stark effects for holes in resonant tunneling devices. Physical Review B, 2006, 74, .	3.2	23
134	Tunneling and magneto-tunnelling effects in n+GaAs/(AlGa)As/n-GaAs/n+GaAs devices. Journal of Physics C: Solid State Physics, 1985, 18, L605-L609.	1.5	22
135	Upconversion electroluminescence in InAs quantum dot light-emitting diodes. Applied Physics Letters, 2008, 92, .	3.3	22
136	High temperature MBE of graphene on sapphire and hexagonal boron nitride flakes on sapphire. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2016, 34, .	1.2	22
137	Resonant tunnelling into the two-dimensional subbands of InSe layers. Communications Physics, 2020, 3, .	5.3	22
138	Study of electronâ€“hole generation and recombination in semiconductors using the Osaka free electron laser. Physica B: Condensed Matter, 2002, 314, 431-436.	2.7	21
139	Voltage-controlled hole spin injection in nonmagneticGaAsâ•AlAsresonant tunneling structures. Physical Review B, 2006, 73, .	3.2	21
140	Deep centre photoluminescence spectra of GaAs(Cr, Si). Journal of Physics C: Solid State Physics, 1978, 11, L771-L775.	1.5	20
141	The observation of a sharp peak in the deep-level photoconductivity spectrum of GaAs(Cr) due to the Cr2+(5T2-5E) 'intracentre' transition. Journal of Physics C: Solid State Physics, 1981, 14, L693-L697.	1.5	20
142	An investigation of the 1.36 eV photoluminescence spectrum of heat-treated InP using Zeeman spectroscopy and strain effects. Journal of Physics C: Solid State Physics, 1984, 17, 1233-1245.	1.5	20
143	A model for the origin of the oscillatory structure in the reverse bias J(V) characteristics of n+GaAs/(AlGa)As/n-GaAs/n+GaAs tunnelling devices. Journal of Physics C: Solid State Physics, 1985, 18, L885-L888.	1.5	20
144	Effect of hydrostatic pressure on the fragmented conduction band structure of dilute Ga(AsN) alloys. Physical Review B, 2005, 72, .	3.2	20

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145	Magnetoanisotropy of electron-correlation-enhanced tunneling through a quantum dot. Physical Review B, 2007, 75, .	3.2	20
146	Photoquantum Hall Effect and Lightâ€Induced Charge Transfer at the Interface of Graphene/InSe Heterostructures. Advanced Functional Materials, 2019, 29, 1805491.	14.9	20
147	Interpretation of the 1.03 eV photoluminescence and absorption in GaP(Cr) in terms of internal transitions of Cr3+. Journal of Physics C: Solid State Physics, 1985, 18, L449-L453.	1.5	19
148	Inverted bistability in the current-voltage characteristics of a resonant tunneling device. Solid-State Electronics, 1989, 32, 1467-1471.	1.4	19
149	Quantum confinement in laterally squeezed resonant tunneling devices. Physical Review Letters, 1992, 69, 2995-2995.	7.8	19
150	Resonance and current instabilities in AlN/GaN resonant tunnelling diodes. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 752-755.	2.7	19
151	Trion formation in narrow GaAs quantum well structures. Physical Review B, 2005, 71, .	3.2	19
152	Raman scattering in InAsâˆ•(AlGa)As self-assembled quantum dots: Evidence of Al intermixing. Applied Physics Letters, 2006, 88, 141905.	3.3	19
153	Probing the intermixing in In(Ga)Asâˆ•GaAs self-assembled quantum dots by Raman scattering. Journal of Applied Physics, 2006, 99, 043501.	2.5	19
154	Fock-Darwin-Like Quantum Dot States Formed by Charged Mn Interstitial Ions. Physical Review Letters, 2008, 101, 226807.	7.8	19
155	MoirÃ©-Modulated Conductance of Hexagonal Boron Nitride Tunnel Barriers. Nano Letters, 2018, 18, 4241-4246.	9.1	19
156	Magnetoresistance effects in laterally confined n-GaAs/(AlGa)As heterostructures. Journal of Physics Condensed Matter, 1989, 1, 10413-10425.	1.8	18
157	Modulation of the luminescence spectra of InAs self-assembled quantum dots by resonant tunneling through a quantum well. Physical Review B, 2000, 62, 13595-13598.	3.2	18
158	Manipulating and Imaging the Shape of an Electronic Wave Function by Magnetotunneling Spectroscopy. Physical Review Letters, 2010, 105, 236804.	7.8	18
159	Van der Waals SnSe 2(1âˆ’ x) S 2 x Alloys: Compositionâ€Dependent Bowing Coefficient and Electronâ€“Phonon Interaction. Advanced Functional Materials, 2020, 30, 1908092.	14.9	18
160	Molecular beam epitaxy growth of GaAs/AlAs double-barrier resonant tunnelling devices on (311)A substrates. Semiconductor Science and Technology, 1992, 7, 267-270.	2.0	17
161	Investigating the cubic anisotropy of the confined hole subbands of an AlAs/GaAs/AlAs quantum well using resonant magnetotunneling spectroscopy. Applied Physics Letters, 1992, 61, 84-86.	3.3	17
162	Electron effective mass and mobility in heavily doped n-GaAsN probed by Raman scattering. Journal of Applied Physics, 2008, 103, 103528.	2.5	17

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163	Electron coherence length and mobility in highly mismatched III-N-V alloys. Applied Physics Letters, 2008, 93, .	3.3	17
164	High-Temperature Molecular Beam Epitaxy of Hexagonal Boron Nitride with High Active Nitrogen Fluxes. Materials, 2018, 11, 1119.	2.9	17
165	Universal conductance fluctuations in the magnetoresistance of submicron n+GaAs wires. Superlattices and Microstructures, 1986, 2, 381-383.	3.1	16
166	Ballistic transport in resonant tunnelling devices with wide quantum wells. Journal of Physics Condensed Matter, 1989, 1, 3025-3030.	1.8	16
167	The effect of the X conduction band minima on resonant tunnelling and charge build-up in double barrier structures based on n-GaAs/(AlGa)As. Solid-State Electronics, 1989, 32, 1731-1735.	1.4	16
168	Optical investigation of charge accumulation and bistability in an asymmetric double barrier resonant tunneling heterostructure. Surface Science, 1990, 228, 373-377.	1.9	16
169	Anisotropy of the confined hole states in a (311)AAlAs/GaAs/AlAs quantum-well system: Evidence for a camelâ€™s-back band structure. Physical Review B, 1992, 46, 15586-15589.	3.2	16
170	Effect of magnetically simulated zero-gravity and enhanced gravity on the walk of the common fruitfly. Journal of the Royal Society Interface, 2012, 9, 1438-1449.	3.4	16
171	An atomic carbon source for high temperature molecular beam epitaxy of graphene. Scientific Reports, 2017, 7, 6598.	3.3	16
172	Magnetophonon spectroscopy of Dirac fermion scattering by transverse and longitudinal acoustic phonons in graphene. Physical Review B, 2019, 100, .	3.2	16
173	Magnetic field and capacitance studies of intrinsic bistability in double-barrier structures. Superlattices and Microstructures, 1989, 6, 59-62.	3.1	15
174	A new technique for directly probing the intrinsic tristability and its temperature dependence in a resonant tunneling diode. Solid-State Electronics, 1994, 37, 961-964.	1.4	15
175	Magnetic-field-induced miniband conduction in semiconductor superlattices. Physical Review B, 2007, 76, .	3.2	15
176	GaAs/(AlGa)As tunnelling devices: Hydrostatic pressure investigation and model for the J(V) characteristics. Surface Science, 1986, 174, 472-477.	1.9	14
177	Ballistic transmission in perpendicular quantum point contacts. Physical Review B, 1989, 40, 10033-10035.	3.2	14
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